

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	102	(gate with ((two dual double twin) near charge near (storage\$1 trap\$4)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/10/05 06:55
L2	5	memory AND substrate AND well\$1 AND (gate ADJ (insulat\$3 oxide dielectric)) AND (gate ADJ electrode) AND ((two dual twin double) NEAR charg\$3 NEAR (storag\$3 trap\$4)) AND (sidewall (side NEAR wall\$1)) AND channel AND ((diffus\$3 dop\$4 implant\$5) NEAR (area\$1 region\$1)) AND current AND (voltage potential) AND (hole\$1 electron\$1).CLM.	US-PGPUB; USPAT	OR	ON	2005/10/05 07:04
S1	6	((("4881108") or ("6434053") or ("6348711")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/06/22 19:33
S2	6	("5999444" "6011725" "6081456" "6137718" "6147904" "6163048").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/06/18 11:48
S3	43	("4173766" "4173791" "4360900" "4380057" "4527257" "4586163" "4630085" "4667217" "4742491" "4847808" "4870470" "5021999" "5159570" "5168334" "5172338" "5214303" "5293563" "5295108" "5305262" "5311049" "5345425" "5349221" "5359554" "5394355" "5412601" "5414693" "5418743" "5424978" "5426605" "5434825" "5440505" "5450341" "5450354" "5477499" "5592417" "5606523" "5654568" "5754475" "5768192" "5793079" "5812449" "5825686" "5841700").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/06/18 12:26
S4	2	("6011725").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/06/18 12:27
S5	4	((("6627498") or ("6335554")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/06/20 10:06
S6	10	("4881108" "5408115" "5422504" "5424979" "5768192" "5780341" "5969383" "6030869" "6040995" "6093605").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/06/20 10:08

S7	7	("5408115" "5614747" "5691937" "5703388" "5729035" "5780891" "5796139").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/06/20 10:14
S8	10	("5120672" "5324675" "5496753" "5830771" "5989957" "6238978" "6255165" "6410957" "6440789" "6486030").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/06/20 10:18
S9	0	voltage near less near than near reference	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/10/04 19:10
S10	0	(potential voltage) near less near than near reference	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/22 19:36
S11	217583	reference near (potential voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/22 19:36
S12	0	(potential voltage) near less near than near reference	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/22 19:36
S13	225	(substrate (well near region)) near reference near (potential voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/22 19:37
S14	89	S13 and memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/22 19:50
S15	14	memory with (substrate (well near region)) near reference near (potential voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/22 19:42
S16	2069	memory with (substrate (well near region)) near (potential voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/22 19:53

S17	1681366	memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/22 19:50
S18	74634	writ\$3 near operat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/22 19:52
S19	60965	S18 and S17	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/22 19:52
S20	209	memory with ((substrate (well near region)) near (potential voltage)) with (source near (potential voltage))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/06/22 19:54
S21	107	S20 and S18	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/10/04 19:15
S22	10	("4881108" "5408115" "5422504" "5424979" "5768192" "5780341" "5969383" "6030869" "6040995" "6093605").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/10/04 19:07
S23	8399	257/239,261,298,314-326,E27.078,E29. 3-E29.309.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/10/04 19:12
S24	5594	438/201,211,216,241,257,258,260-266,591, 593.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/10/04 19:13
S25	12633	S23 or S24	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/10/04 19:13

S26	1	S25 and ((gate near electrode) with ((two dual double twin) near charge near (storage\$1 trap\$4)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/10/04 19:26
S27	8	((gate near electrode) with ((two dual double twin) near charge near (storage\$1 trap\$4)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/10/04 19:17
S28	43	S25 and (gate with ((two dual double twin) near charge near (storage\$1 trap\$4)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/10/04 19:27